

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	78	("20010009784" "20020074598" "20020086472" "20020086497" "20020090791" "20030032261" "20030040158" "20030057184" "20030067035" "3602841" "4665415" "4853076" "4855245" "4952524" "4958213" "5006913" "5060030" "5081513" "5108843" "5134085" "5330446" "5354695" "5371399" "5391510" "5459346" "5471948" "5557122" "5561302" "5565697" "5571741" "5592007" "5592018" "5670798" "5679965" "5683934" "5840593" "5861651" "5880040" "5940736" "5946559" "5960297" "5989978" "6008126" "6025280" "6046464" "6066545" "6090684" "6107143" "6117722" "6133071" "6165383" "6221735" "6228694" "6246095" "6255169" "6261964" "6265317" "6274444" "6281532" "6284623" "6284626" "6319794" "6361885" "6362082" "6368931" "6403486" "6403975" "6406973" "6461936" "6476462" "6493497" "6498358" "6501121" "6506652" "6509618" "6521964" "6531369" "6531740").PN.	US-PGPUB; USPAT	OR	OFF	2005/09/16 11:23
L2	3	"5310446".pn."5241197".pn."5019882".pn.	US-PGPUB; USPAT	OR	OFF	2005/09/16 11:07
L3	5	"4665415".pn."4952524".pn."4855245".pn."4853076".pn."3602841".pn.	US-PGPUB; USPAT	OR	OFF	2005/09/16 11:52
L4	2253	438/199.ccIs. 438/218.ccIs. 438/221.ccIs. 438/514.ccIs. 438/739.ccIs. 438/766.ccIs.	US-PGPUB; USPAT	OR	OFF	2005/09/16 11:53
L5	186	438/218.ccIs.	US-PGPUB; USPAT	OR	OFF	2005/09/16 12:25
L6	1	"6825086".pn.	US-PGPUB; USPAT	OR	OFF	2005/09/16 12:39
L7	11443	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio. sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens\$6 compress\$6)	US-PGPUB; USPAT	OR	ON	2005/09/16 12:56

L8	724	7 same (cmos nmos pmos nfet pfet "n-type" "p-type") same (semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2005/09/16 12:59
L9	383	8 same (etch\$6 gap groove trench slot hole opening)	US-PGPUB; USPAT	OR	ON	2005/09/16 12:58
L10	175	4 and 7	US-PGPUB; USPAT	OR	ON	2005/09/16 13:13
L11	2654	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio. sub.x n.sub.y" "sio.sub.xn.sub.y") with (strain stress tens\$6 compress\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 12:53
L12	157	11 and (cmos nmos pmos nfet pfet "n-type" "p-type") and (semiconductor substrate wafer silicon)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 12:55
L13	859	11 and (etch\$6 gap groove trench slot hole opening dop\$6 implant\$8)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 12:55
L14	88	13 and (cmos nmos pmos nfet pfet "n-type" "p-type") and (semiconductor substrate wafer silicon)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:56
L15	1220	((silicon adj (germanium oxide dioxide nitride oxynitride)) sige gesi "sio.sub.2" sin sion "si.sub.3 n.sub.4" sio "si.sub.3n.sub.4" "sio. sub.x n.sub.y" "sio.sub.xn.sub.y") with ((strain stress tens\$6 compress\$6) near (layer film))	US-PGPUB; USPAT	OR	ON	2005/09/16 12:56
L16	79	15 same (cmos nmos pmos nfet pfet "n-type" "p-type") same (semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2005/09/16 15:31
L17	424	15 same (etch\$6 gap groove trench slot hole opening dop\$6 implant\$6)	US-PGPUB; USPAT	OR	ON	2005/09/16 13:01
L18	388	17 same (cmos nmos pmos nfet pfet "n-type" "p-type" semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2005/09/16 12:59
L19	387	17 same (semiconductor substrate wafer silicon)	US-PGPUB; USPAT	OR	ON	2005/09/16 12:59
L20	52	17 same (cmos nmos pmos nfet pfet "n-type" "p-type")	US-PGPUB; USPAT	OR	ON	2005/09/16 13:00

L21	95	15 same (etch\$6 remov\$6) same (gap groove trench slot hole opening dop\$6 implant\$6)	US-PGPUB; USPAT	OR	ON	2005/09/16 16:17
S2	1	"6831292".pn.	US-PGPUB; USPAT	OR	OFF	2005/09/09 11:28